

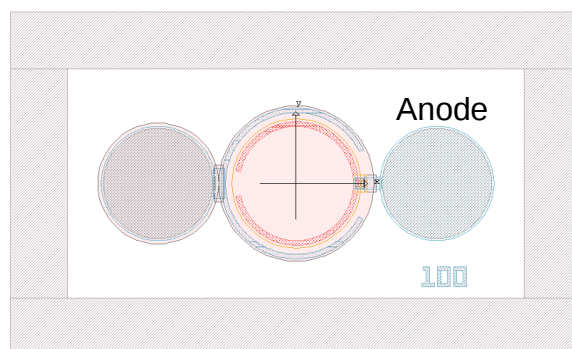
GCS GaAs PIN Photodiodes for 1-4 Gb/sec Applications



850 nm GaAs PIN PD

- Mesa Diode on Semi-Insulating Substrates
- Anode/Cathode Bonding Pads on Front Side
- Low Dark Current & Capacitance with High Responsivity
- Bandwidths up to 5 GHz
- Customer Specified Configurations Available

Part Number: Do007_100um_PIN4	
PHYSICAL	Typical
Aperture Dia.	100 μ m
Bonding Pad Dia.	100 μ m
Die Height	100-120 μ m
Die Size	500 μ m X 300 μ m
Substrate	Semi-Insulating



Applications

- Short Reach Optical Networks
- 1 to 4 Gigabit Ethernet, Fiber Channel

Key Benefits

- Low-Cost 4-inch Manufacturing
- Fast Cycle-Times
- CAD Support & Mask Procurement
- Robust Process

Mask ID: Do007 (100 μ m)						
CHARACTERISTICS	Conditions	Min.	Typical	Max	Unit	Notes
Bandwidth	-3V	-	5	-	GHz	
Wavelength Range	-3V	760	850	860	nm	
Responsivity	-3V	0.5	0.6	-	A/W	@ 850nm
Dark Current	-3V	-	0.1	0.5	nA	
Reverse Breakdown	-20V	-	-	1	μ A	
Capacitance	-3V	-	0.35	0.4	pF	